Title (en)

METHOD FOR DOPING ONE SIDE OF A SEMICONDUCTOR BODY

Title (de)

VERFAHREN ZUR EINSEITIGEN DOTIERUNG EINES HALBLEITERKÖRPERS

Title (fr)

PROCEDE PERMETTANT DE DOPER D'UN SEUL COTE UN DISPOSITIF A SEMI-CONDUCTEUR

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Application

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Abstract (en)

[origin: DE19813188A1] The invention relates to a method for doping one side of semiconductor bodies, especially of silicon wafers. To this end, a conventional oxide layer (2, 3) is firstly deposited on both the side (DS) of the substrate (1) to be doped and on the side (GS) of a substrate (1) which is not to be doped. Afterwards, a doping layer (4) containing the doping agent is deposited on the oxide layer (3) of the side (DS) which is to be doped. In a diffusion step, the doping agent firstly passes in a uniform manner through the oxide layer (3) located between the substrate (1) and the doped layer (4). The doping agent then penetrates the substrate (1), and produces a uniform doping.

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